

2SC1624

2SC1625

SILICON NPN PLANAR TYPE

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07453 D T-33-07

Unit in mm

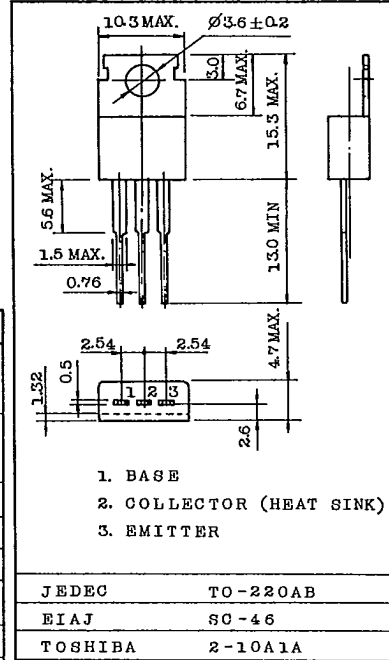
MEDIUM POWER AMPLIFIER APPLICATIONS.
DRIVER STAGE AMPLIFIER APPLICATIONS.

FEATURES:

High Breakdown Voltage : $V_{CE0}=120V$ (2SC1624)
Complementary to 2SA814 and 2SA815.

MAXIMUM RATINGS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	2SC1624	120	V
	2SC1625	100	
Collector-Emitter Voltage	2SC1624	120	V
	2SC1625	100	
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Emitter Current	I_E	-1	A
Collector Power Dissipation ($T_c=25^\circ C$)	P_C	15	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=50V, I_E=0$	-	-	1.0	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	1.0	μA
Collector-Emitter Breakdown Voltage	2SC1624	$I_C=10mA, I_B=0$	120	-	-	V
	2SC1625		100	-	-	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	5	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=5V, I_C=150mA$	70	-	240	
	$h_{FE(2)}$	$V_{CE}=5V, I_C=500mA$	40	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$	-	-	0.5	V
Base-Emitter Voltage	V_{BE}	$V_{CE}=5V, I_C=500mA$	-	-	1.0	V
Transition Frequency	f_T	$V_{CE}=5V, I_C=150mA$	10	30	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=1 MHz$	-	20	-	pF

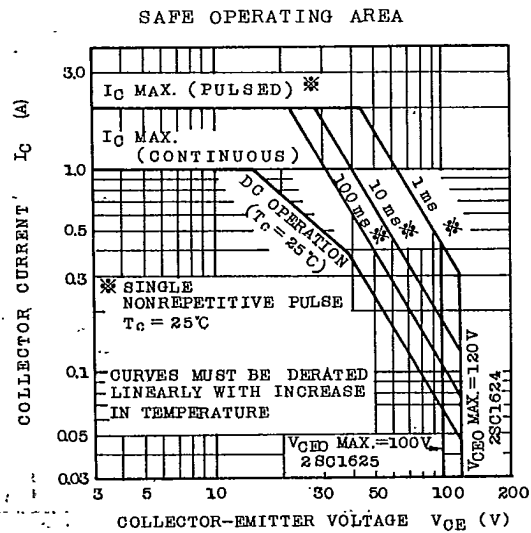
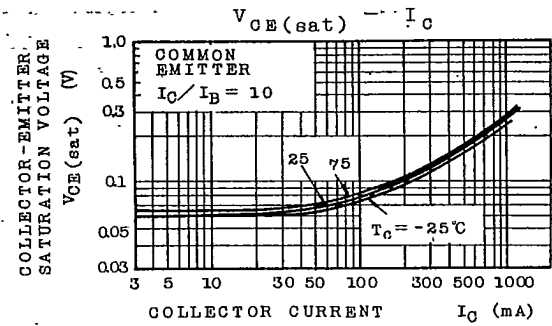
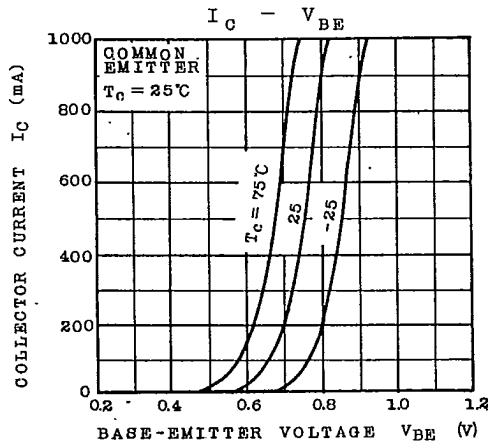
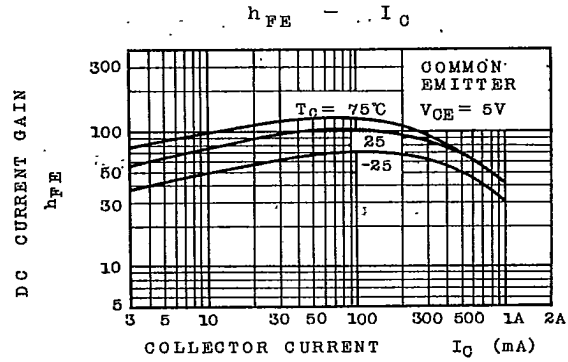
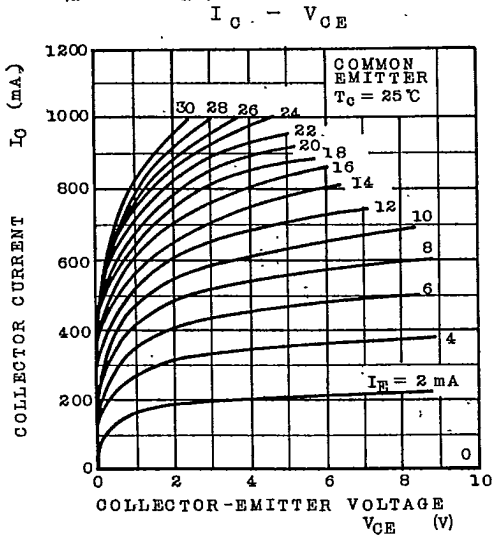
Note : $h_{FE(1)}$ Classification : 0 : 70~140, Y : 120~240

TOSHIBA CORPORATION

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